256MB - 32Mx72 SDRAM UNBUFFERED

FEATURES

- PC100 and PC133 Compatible
- Burst Mode Operation
- Auto and Self Refresh capability
- LVTTL compatible inputs and outputs
- Serial Presence Detect with EEPROM
- Fully synchronous: All signals are registered on the positive edge of the system clock
- Programmable Burst Lengths: 1, 2, 4, 8 or Full Page
- 3.3V ± 0.3V Power Supply
- 144 Pin SO-DIMM JEDEC
  - Package height options:
    JD1: 31.75 (1.25")

DESCRIPTION

The W3DG7232V is a 32Mx72 synchronous DRAM module which consists of nine 32Mx8 SDRAM components in TSOP II package, and one 2K EEPROM in an 8 pin TSSOP package for Serial Presence Detect which are mounted on a 144 Pin SO-DIMM multilayer FR4 Substrate.

* This product is under development, is not qualified or characterized and is subject to change without notice.

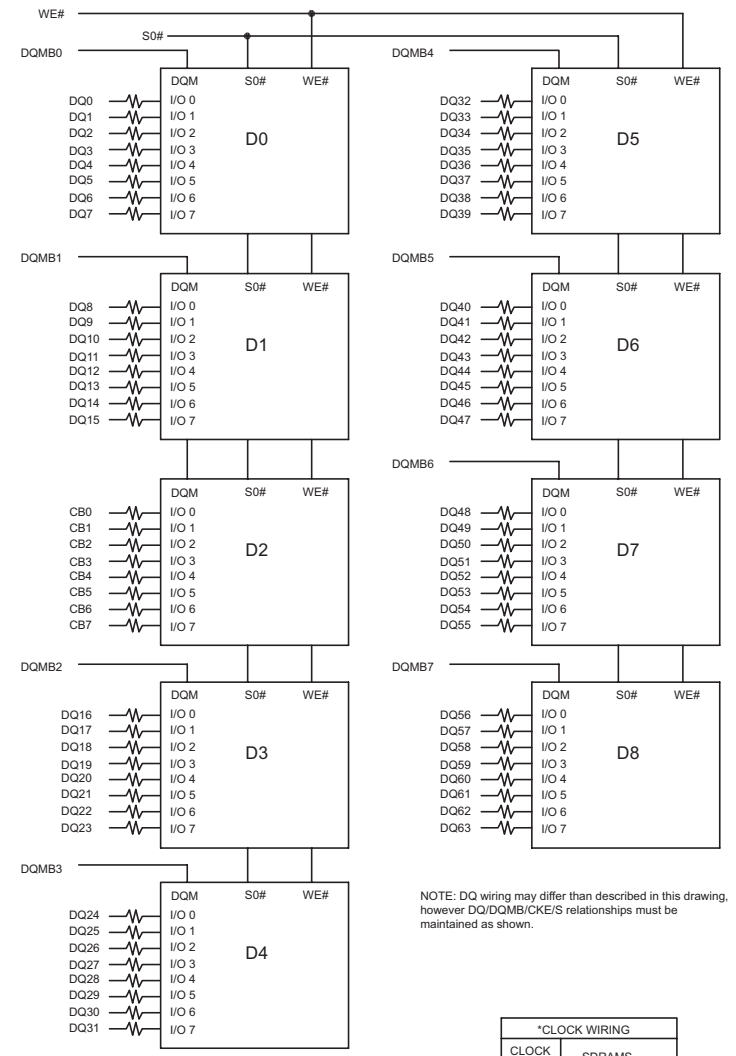
PIN CONFIGURATIONS (FRONT SIDE/BACK SIDE)

PIN	FRONT	PIN	BACK	PIN	FRONT	PIN	BACK	PIN	FRONT	PIN	BACK
1	Vss	2	Vss	49	DQ13	50	DQ45	97	DQ22	98	DQ54
3	DQ0	4	DQ32	51	DQ14	52	DQ46	99	DQ23	100	DQ55
5	DQ1	6	DQ33	53	DQ15	54	DQ47	101	Vcc	102	Vcc
7	DQ2	8	DQ34	55	Vss	56	Vss	103	A6	104	A7
9	DQ3	10	DQ35	57	CB0	58	CB4	105	A8	106	BA0
11	Vcc	12	Vcc	59	CB1	60	CB5	107	Vss	108	Vss
13	DQ4	14	DQ36	61	CLK0	62	CKE0	109	A9	110	BA1
15	DQ5	16	DQ37	63	Vcc	64	Vcc	111	A10	112	A11
17	DQ6	18	DQ38	65	RAS#	66	CAS#	113	Vcc	114	Vcc
19	DQ7	20	DQ39	67	WE#	68	NC	115	DQMB2	116	DQMB6
21	Vss	22	Vss	69	SO#	70	A12	117	DQMB3	118	DQMB7
23	DQMB0	24	DQB4	71	NC	72	NC	119	Vss	120	Vss
25	DQMB1	26	DQB5	73	NC	74	CLK1	121	DQ24	122	DQ56
27	Vcc	28	Vcc	75	Vss	76	Vss	123	DQ25	124	DQ57
29	A0	30	A3	77	CB2	78	CB6	125	DQ26	126	DQ58
31	A1	32	A4	79	CB3	80	CB7	127	DQ27	128	DQ59
33	A2	34	A5	81	Vcc	82	Vcc	129	Vcc	130	Vcc
35	Vss	36	Vss	83	DQ16	84	DQ48	131	DQ28	132	DQ60
37	DQ8	38	DQ40	85	DQ17	86	DQ49	133	DQ29	134	DQ61
39	DQ9	40	DQ41	87	DQ18	88	DQ50	135	DQ30	136	DQ62
41	DQ10	42	DQ42	89	DQ19	90	DQ51	137	DQ31	138	DQ63
43	DQ11	44	DQ43	91	VSS	92	Vss	139	Vss	140	Vss
45	Vcc	46	Vcc	93	DQ20	94	DQ52	141	SDA	142	SCL
47	DQ12	48	DQ44	95	DQ21	96	DQ53	143	Vcc	144	Vcc

PIN NAMES

A0 – A12	Address input (Multiplexed)
BA0-1	Select Bank
DQ0-63	Data Input/Output
CB0-7	Check bit (Data-in/data-out)
CLK0,CK1	Clock input
CKE0	Clock Enable input
CS0#	Chip select Input
RAS#	Row Address Strobe
CAS#	Column Address Strobe
WE#	Write Enable
DQMB0-7	DQM
Vcc	Power Supply (3.3V)
Vss	Ground
SDA	Serial data I/O
SCL	Serial clock
DNU	Do not use
NC	No Connect

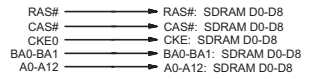
FUNCTIONAL BLOCK DIAGRAM

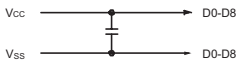


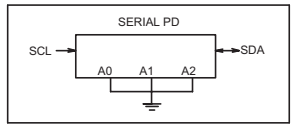
NOTE: DQ wiring may differ than described in this drawing, however DQ/DQMB/CKE/S relationships must be maintained as shown.

*CLOCK WIRING	
CLOCK INPUT	SDRAMS
*CLK0	4 OR 5 SDRAMS
*CLK1	4 OR 5 SDRAMS

*Wire per Clock Loading Table/Wiring Diagrams







ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Units
Voltage on any pin relative to V_{SS}	V_{IN}, V_{OUT}	-1.0 ~ 4.6	V
Voltage on V_{CC} supply relative to V_{SS}	V_{CC}, V_{CCQ}	-1.0 ~ 4.6	V
Storage Temperature	T_{STG}	-55 ~ +150	°C
Power Dissipation	P_D	9	W
Short Circuit Current	I_{OS}	50	mA

Note: Permanent device damage may occur if "ABSOLUTE MAXIMUM RATINGS" are exceeded.
Functional operation should be restricted to recommended operating condition.
Exposure to higher than recommended voltage for extended periods of time could affect device reliability.

RECOMMENDED DC OPERATING CONDITIONS

Voltage Referenced to: V_{SS} = 0V, 0°C ≤ T_A ≤ +70°C

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply Voltage	V_{CC}	3.0	3.3	3.6	V	
Input High Voltage	V_{IH}	2.0	3.0	$V_{CCQ+0.3}$	V	1
Input Low Voltage	V_{IL}	-0.3	—	0.8	V	2
Output High Voltage	V_{OH}	2.4	—	—	V	I_{OH}= -2mA
Output Low Voltage	V_{OL}	—	—	0.4	V	I_{OL}= -2mA
Input Leakage Current	I_{LI}	-10	—	10	µA	3

Note:
1. V_{IH} (max)= 5.6V AC. The overshoot voltage duration is ≤ 3ns.
2. V_{IL} (min)= -2.0V AC. The undershoot voltage duration is ≤ 3ns.
3. Any input 0V ≤ V_{IN} ≤ V_{CCQ}
Input leakage currents include Hi-Z output leakage for all bi-directional buffers with Tri-State outputs.

CAPACITANCE

T_A = 25°C, f = 1MHz, V_{CC} = 3.3V, V_{REF} = 1.4V ± 200mV

Parameter	Symbol	Max	Unit
Input Capacitance (A0-A12)	C_{IN1}	50	pF
Input Capacitance (RAS#,CAS#,WE#)	C_{IN2}	50	pF
Input Capacitance (CKE0)	C_{IN3}	50	pF
Input Capacitance (CK0)	C_{IN4}	22	pF
Input Capacitance (CS0#)	C_{IN5}	50	pF
Input Capacitance (DQM0-DQM7)	C_{IN6}	8	pF
Input Capacitance (BA0-BA1)	C_{IN7}	50	pF
Data Input/Output Capacitance (DQ0-DQ63)	C_{OUT}	9.5	pF
Data input/output capacitance (CB0-CB7)	C_{OUT1}	9.5	pF

OPERATING CURRENT CHARACTERISTICS

V_{CC} = 3.3V, 0°C ≤ T_A ≤ +70°C

			Version		
Parameter	**Symbol**	**Conditions**	**100/133**	**Units**	**Note**
Operating Current (One bank active)	I_{CC1}	Burst Length = 1 $t_{RC} \leq t_{RC}$(min) I_{OL} = 0mA	900	mA	1
Precharge Standby Current in Power Down Mode	I_{CC2P}	CKE ≤ V_{IL}(max), t_{CC} = 10ns	18	mA	
	I_{CC2PS}	CKE & CK ≤ V_{IL}(max), t_{CC} = ∞	18		
Precharge Standby Current in Non-Power Down Mode	I_{CC2N}	CKE ≥ V_{IH}(min), CS ≥ V_{IH}(min), tcc =10ns Input signals are charged one time during 20	180	mA	
	I_{CC2NS}	CKE ≥ V_{IH}(min), CK ≥V_{IL}(max), t_{CC} = ∞ Input signals are stable	90		
Active Standby Current in Power-Down Mode	I_{CC3P}	CKE ≥ V_{IL}(max), t_{CC} = 10ns	54	mA	
	I_{CC3PS}	CKE & CK ≤ V_{IL}(max), t_{CC} = ∞	54		
Active Standby Current in Non-Power Down Mode	I_{CC3N}	CKE ≥ V_{IH}(min), CS ≥ V_{IH}(min), tcc = 10ns Input signals are changed one time during 20ns	270	mA	
	I_{CC3NS}	CKE ≥ V_{IH}(min), CK ≤ V_{IL}(max), tcc = ∞ Input signals are stable	225	mA	
Operating Current (Burst mode)	I_{CC4}	Io = mA Page burst 4 Banks activated t_{CCD} = 2CK	990	mA	1
Refresh Current	I_{CC5}	$t_{RC} \geq t_{RC}$(min)	1980	mA	2
Self Refresh Current	I_{CC6}	CKE ≤ 0.2V	27	mA	

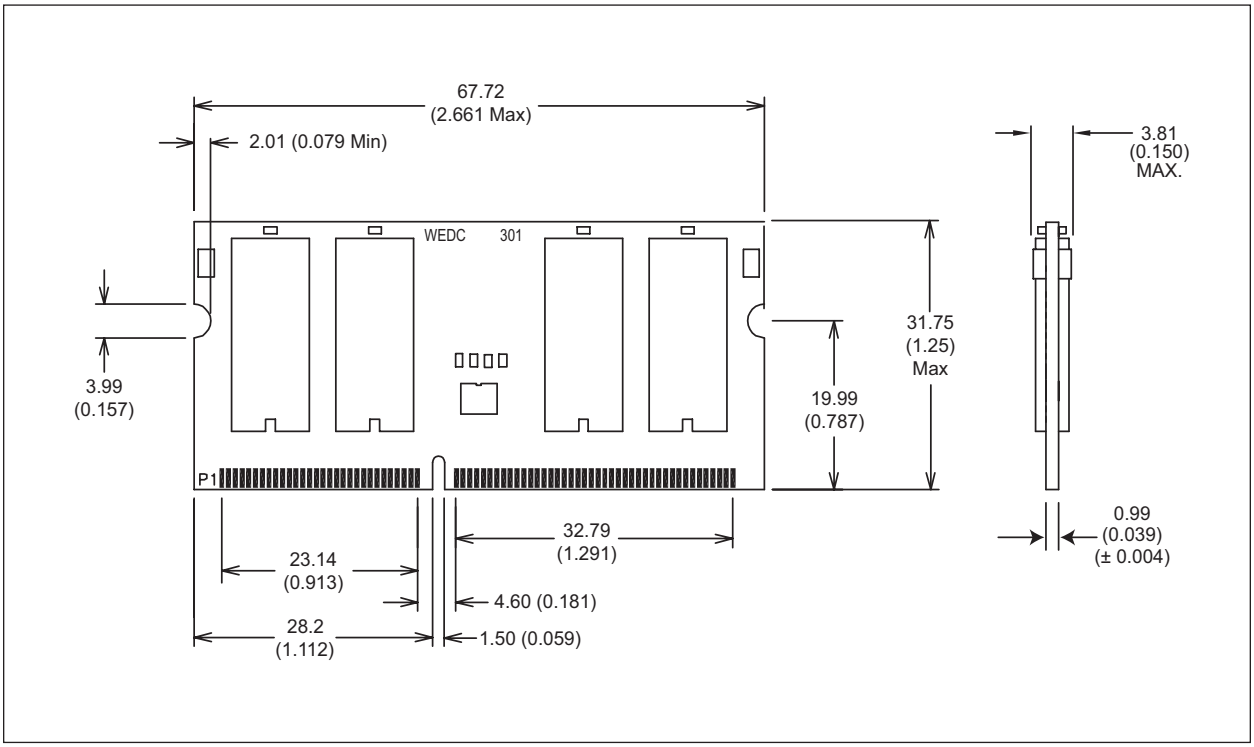
Notes:
1. Measured with outputs open.
2. Refresh period is 64ms.

PACKAGE DIMENSIONS FOR JD1

Ordering Information	Speed	CAS Latency	Height*
W3DG7232V10JD1	100MHz	CL=2	31.75 (1.25")
W3DG7232V7JD1	133MHz	CL=2	31.75 (1.25")
W3DG7232V75JD1	133MHz	CL=3	31.75 (1.25")

Note: For industrial temperature range product, add an "I" to the end of the part number.

PACKAGE DIMENSIONS FOR JD1



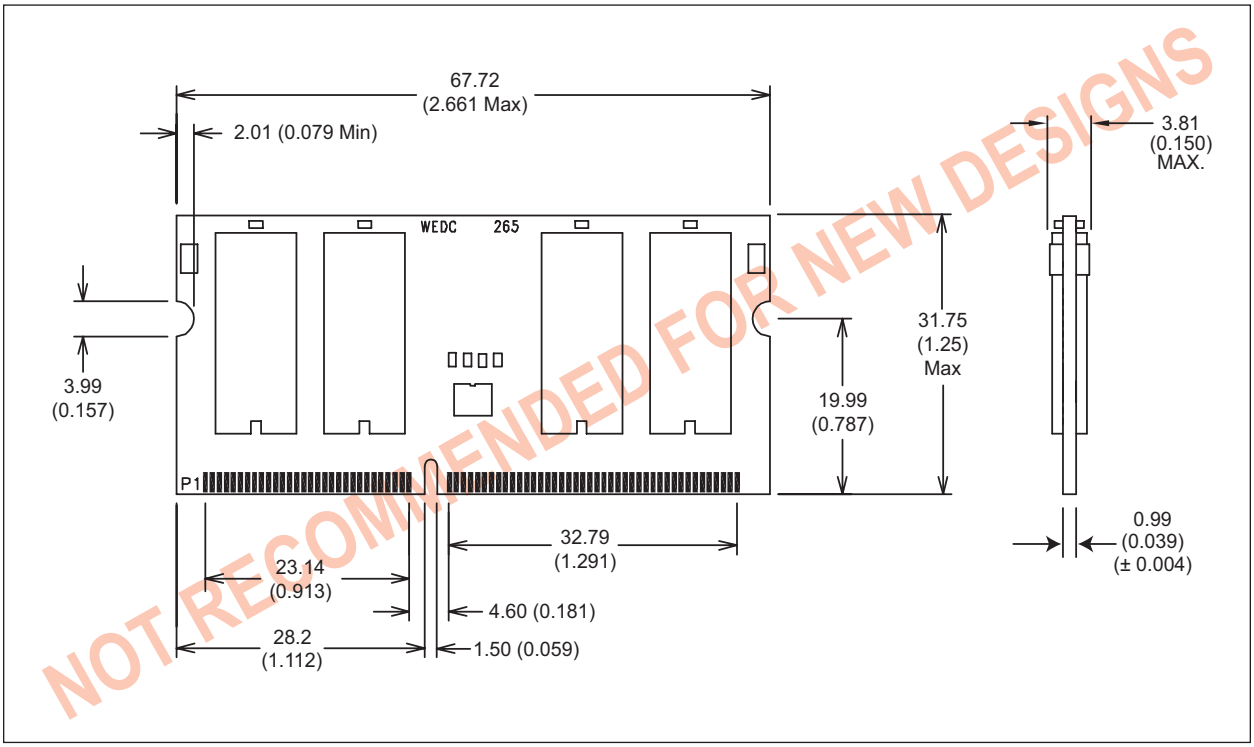
*** ALL DIMENSIONS ARE IN MILLIMETERS AND (INCHES).**

PACKAGE DIMENSIONS FOR D1

Ordering Information	Speed	CAS Latency	Height*
W3DG7232V10D1	100MHz	CL=2	31.75 (1.25")
W3DG7232V7D1	133MHz	CL=2	31.75 (1.25")
W3DG7232V75D1	133MHz	CL=3	31.75 (1.25")

Note: For industrial temperature range product, add an "I" to the end of the part number.

PACKAGE DIMENSIONS FOR D1



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Document Title

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Revision History

Rev #	History	Release Date	Status
Rev A	A.1 Changed the module height to 1.095" A.2 Changed part number to WED3DG7232V-AD1	6-2-03	Advanced
Rev 0	0.1 Updated CAP and I_{DD} Spec. 0.2 Created document title page 0.3 Moved from Advanced to Preliminary 0.4 Removed "ED" from part number	9-04	Preliminary